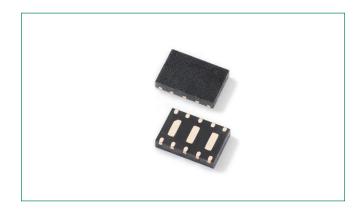
AQ2555NUTG 2.5V 45A Diode Array





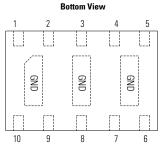
Description

The AQ2555NUTG is a low-capacitance, TVS Diode Array designed to provide protection against ESD (electrostatic discharge), CDE (cable discharge events), EFT (electrical fast transients), and lightning induced surges for highspeed, differential data lines. It's packaged in a µDFN package (3.0 x 2.0mm) and each component can protect up 4 channels or 2 differential pairs, up to 45A (IEC 61000-4- 5 2nd edition,) and up to 30kV ESD (IEC 61000-4-2). The "flow-through" design minimizes signal distortion, reduces voltage overshoot, and provides a simplified PCB design.

The AQ2555NUTG with its low capacitance and low clamping voltage makes it ideal for high-speed data interfaces such as 1GbE applications found in notebooks, switches, etc.

Pinout

Top View GND GND GND

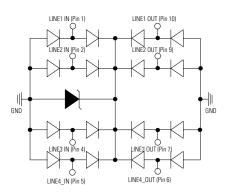


Note: PIN3, PIN8 are same potential with GND

Features

- ESD, IEC 61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC 61000-4-4, 50A (5/50ns)
- Lightning, IEC 61000-4-5 2nd edition, 45A $(t_n = 8/20 \mu s)$
- · Low capacitance of 2.5pF@0V (TYP) per I/O
- Low leakage current of 0.1µA (TYP) at 2.5V
- PPAP capable

- µDFN-10 package is optimized for high-speed data line routing
- Provides protection for two differential data pairs (4 channels) up to 45A
- · Low operating and clamping voltage
- AEC-Q101 qualified
- Halogen free, Lead free and RoHS compliant
- Moisture Sensitivity Level(MSL -1)



Functional Block Diagram

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Applications

- •10/100/1000 Ethernet
- WAN/LAN Equipment
- Desktops, Servers and Notebooks
- LVDS Interfaces
- Integrated Magnetics
- Automotive Application

Application Example

RJ-45 Connector **Ethernet PHY** TP0+ TPO-TP1+ TP1-TP2+ TP2-TP3+ TP3-AQ2555



TVS Diode Array (SPA®Diodes) Lightning Surge Protection - AQ2555NUTG

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
l _{pp}	Peak Current (t _p =8/20µs)	45	А
P_{Pk}	Peak Pulse Power (t _o =8/20µs)	1000	W
T _{OP}	Operating Temperature	-40 to 150	°C
T _{STOR}	Storage Temperature	-55 to 150	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

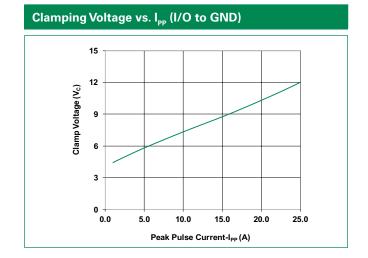
Electrical Characteristics (T_{OP}=25°C)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units	
Reverse Standoff Voltage	V _{RWM}	I _R ≤ 1μA			2.5	V	
Reverse Leakage Current	I _R	V _{RWM} = 2.5V, T = 25°C		0.1	0.5	μА	
Snap Back Voltage	V _{SB}	$I_{SB} = 50 \text{mA}$ 2.0				V	
		I_{pp} = 1A, t_p = 8/20 μ s, Any I/O to Ground		4.5			
		$I_{pp} = 10A$, $t_p = 8/20\mu s$, Any I/O to Ground		7.5		V	
Clamp Voltage	V _c	$I_{pp} = 25A$, $t_p = 8/20\mu s$, Any I/O to Ground		12			
		I _{pp} = 45A, t _p = 8/20µs, Line-to-Line ¹ , two I/O Pins connected together on each line		19			
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns, Any I/O to Ground		0.1		Ω	
E00.14(1)		IEC 61000-4-2 (Contact)	±30			kV	
ESD Withstand Voltage	V _{ESD}	IEC 61000-4-2 (Air)	±30			kV	
Diode Capacitance	C _{I/O to GND}	Between I/O Pins and Ground $V_R = 0V$, $f = 1MHz$		2.5		pF	
	C _{I/O to I/O}	Between I/O Pins V _B = 0V, f = 1MHz		1.2		pF	

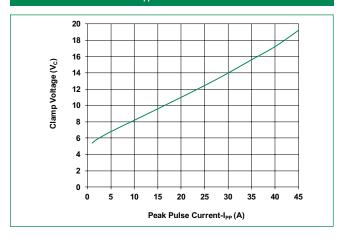
^{1.} Rating with 2 pins connected together per sugguested diagram (For example, pin1 is connected to pin 10, pin 2 is connected to Pin 9, Pin 4 is connected to pin 7 and pin 5 is connected to pin 6) 2. Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window t1=70ns to t2=90ns



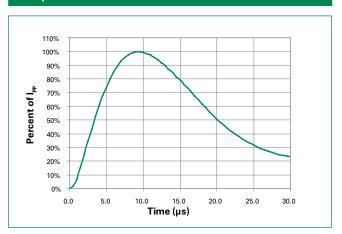
5.0 4.0 3.0 1.0 0.0 0.0 0.5 1 1.5 2 2.5 Bias Voltage (V)



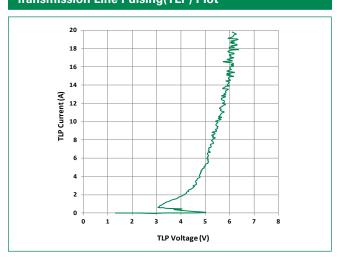
Clamping Voltage vs. I_{PP} (Line-to-Line)



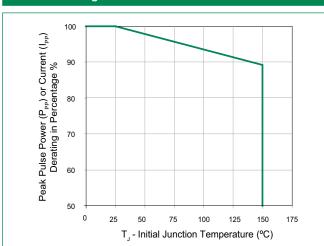
8/20µs Pulse Waveform



Transmission Line Pulsing(TLP) Plot



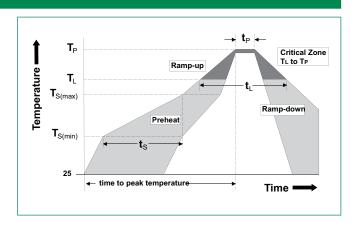
Power Derating Curve



TVS Diode Array (SPA®Diodes)

Soldering Parameters

Reflow Con	Pb – Free assembly		
Pre Heat	- Temperature Min (T _{s(min)})	150°C	
	-Temperature Max (T _{s(max)})	200°C	
	-Time (min to max) (t _s)	60 – 180 secs	
Average ran	3°C/second max		
T _{S(max)} to T _L - Ramp-up Rate		3°C/second max	
Reflow	- Temperature (T _L) (Liquidus)	217°C	
	- Temperature (t _L)	60 – 150 seconds	
Peak Tempe	260+0/-5 °C		
Time within	20 - 40 seconds		
Ramp-dowi	6°C/second max		
Time 25°C t	8 minutes Max.		
Do not exce	260°C		



Ordering Information

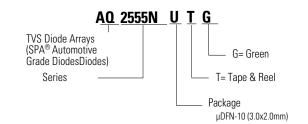
Part Number	Package	Min. Order Qty.	
AQ2555NUTG	μDFN-10 (3.0x2.0mm)	3000	

Product Characteristics

Lead Plating	Pre-Plated Frame	
Lead Material	Copper Alloy	
Substrate material	Silicon	
Body Material	Molded Compound	
Flammability	UL Recognized compound meeting flammability rating V-0	

- **Notes:**1. All dimensions are in millimeters
- Dimensions include solder plating.
 Dimensions are exclusive of mold flash & metal burr.

Part Numbering System

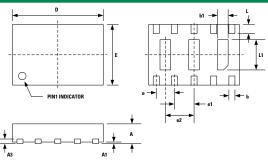


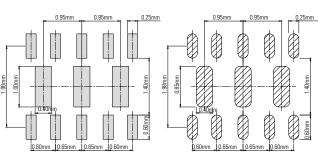
Part Marking System



TVS Diode Array (SPA®Diodes)

Package Dimensions — µDFN-10 (3.0x2.0mm)





Recommended Soldering Pads Layout Recommended Stencil Apertures
Recommended Stencil thickness 5mils

Package	μDFN-10 (3.0x2.0mm)						
JEDEC	MO-229						
Compleal	Millimeters			Inches			
Symbol	Min	Nom	Max	Min	Nom	Max	
Α	0.50	0.60	0.65	0.020	0.024	0.026	
A1	0.00	0.03	0.05	0.000	0.001	0.002	
А3	0.15 Ref			0.006 Ref			
b	0.15	0.20	0.25	0.006	0.008	0.010	
b1	0.25	0.35	0.45	0.010	0.014	0.018	
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	1.90	2.00	2.10	0.075	0.079	0.083	
е	0.60 BSC			0	.024 BSC		
e1	0.65 BSC			0	.026 BSC		
e2	0.95 BSC				0.037		
L	0.25	0.30	0.35	0.010	0.012	0.014	
L1	0.95	1.00	1.05	0.037	0.039	0.041	

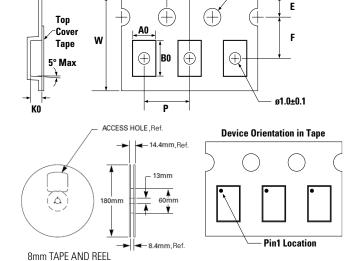
Notes :

- 1. All dimensions are in millimeters
- 2. Dimensions include solder plating.
- 3. Dimensions are exclusive of mold flash & metal burr.

Tape & Reel Specification — µDFN-10 (3.0x2.0mm)

T→||←

ø1.55±0.05



Package	μDFN-10 (3.0x2.0mm)		
Symbol	Millimeters		
A0	2.30 +/- 0.10		
В0	3.20 +/- 0.10		
E	1.75 +/- 0.10		
F	3.50 +/- 0.05		
K0	1.0 +/- 0.10		
Р	4.00 +/- 0.10		
P0	4.00 +/- 0.10		
P2	2.00 +/- 0.10		
Т	0.3 +/- 0.05		
W	8.00 +0.30/- 0.10		

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